TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM6N15FU

# High Speed Switching Applications Analog Switching Applications

• Small package

• Low ON resistance :  $R_{on} = 4.0 \Omega \text{ (max) } (@V_{GS} = 4 \text{ V})$ 

:  $R_{on} = 7.0 \Omega \text{ (max) } (@V_{GS} = 2.5 \text{ V})$ 

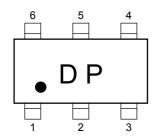
### Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

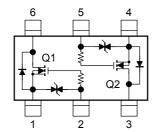
Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		$V_{DS}$	30	V	
Gate-Source voltage		$V_{GSS}$	±20	V	
Drain current	DC	I <sub>D</sub>	100	mA	
	Pulse	I <sub>DP</sub>	200		
Drain power dissipation (Ta = 25°C)		P <sub>D</sub> (Note)	200	mW	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−55~150</b>	°C	

Note: Total rating

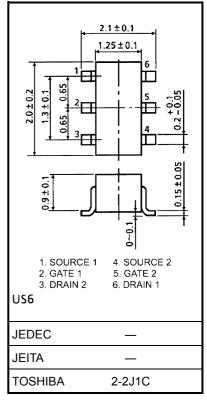
#### Marking

## **Equivalent Circuit (top view)**





Unit: mm



Weight: 6.8 mg (typ.)

# **Handling Precaution**

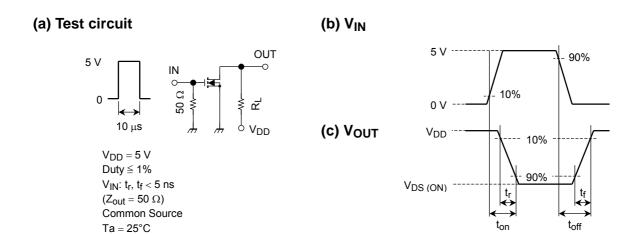
When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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#### Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$	_	_	±1	μΑ	
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 0.1 \text{ mA}, V_{GS} = 0$	30	_	_	V	
Drain cut-off current		I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0$	_	_	1	μΑ	
Gate threshold voltage		$V_{th}$	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.8	_	1.5	V	
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$	25	_	_	mS	
Drain-Source ON resistance		R <sub>DS (ON)</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 4 V	_	2.2	4.0	Ω	
			I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 2.5 V	_	4.0	7.0	5.2	
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 3 V, V <sub>GS</sub> = 0, f = 1 MHz	_	7.8	_	pF	
Reverse transfer capacitance		C <sub>rss</sub>		_	3.6	_	pF	
Output capacitance		Coss		_	8.8	_	pF	
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 5 \text{ V}, I_D = 10 \text{ mA},$	_	50	_	ns	
	Turn-off time	t <sub>off</sub>	V <sub>GS</sub> = 0~5 V	_	180	—		

# **Switching Time Test Circuit**



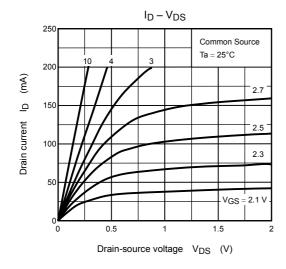
#### **Precaution**

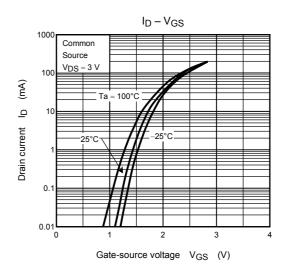
 $V_{th}$  can be expressed as voltage between gate and source when low operating current value is  $I_D$  = 100  $\mu A$  for this product. For normal switching operation,  $V_{GS}$  (on) requires higher voltage than  $V_{th}$  and  $V_{GS}$  (off) requires lower voltage than  $V_{th}$ . (Relationship can be established as follows:  $V_{GS}$  (off) <  $V_{th}$  <  $V_{GS}$  (on))

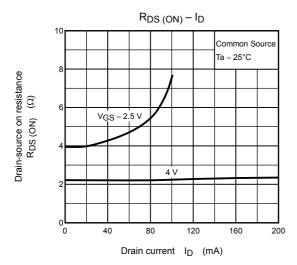
Please take this into consideration for using the device.  $V_{\rm GS}$  recommended voltage of 2.5 V or higher to turn on this product.

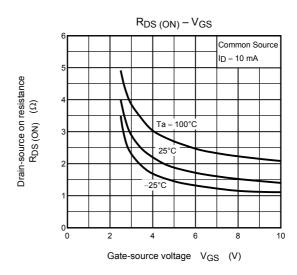
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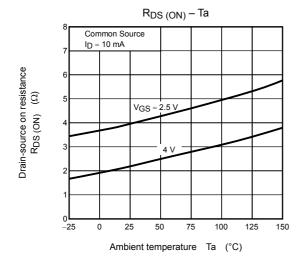
#### (Q1, Q2 Common)

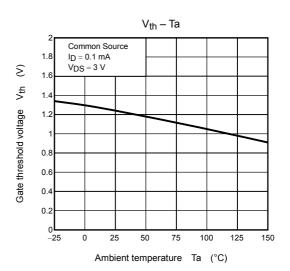






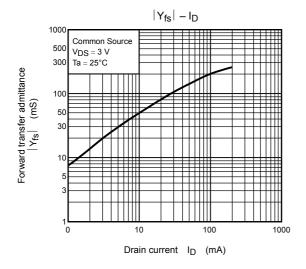


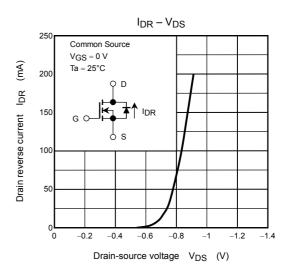


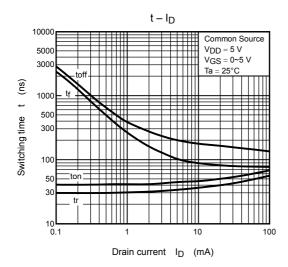


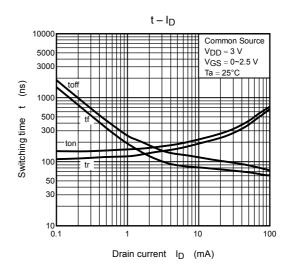
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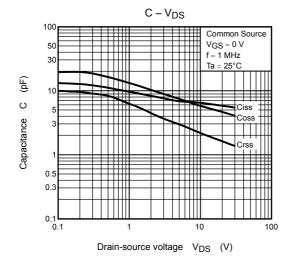
#### (Q1, Q2 Common)

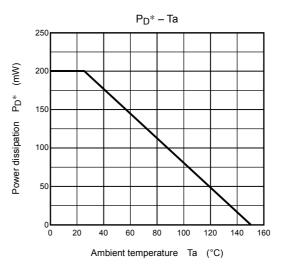












\*: Total rating

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